# MSKSEMI 美森科







99



MOV



GDT



DIED

**BSS138W-7-F-MS** 

**Product specification** 





#### **General Features**

- 55V,300mA, RDS(ON) =1.2Ω@VGS = 10V
- Improved dv/dt capability
- Fast switching
- Green Device Available

# **Application**

- Notebook
- Load Switch
- Battery Protection
- Hand-held Instruments

#### **Reference News**

PACKAGE OUTLINE	Pin Configuration	Marking
	G · Y	138W
SOT-323	s	



# Absolute Maximum Ratings Tc=25℃ unless otherwise noted

Symbol	Parameter	Rating	Units
V <sub>DS</sub>	Drain-Source Voltage	55	V
Vgs	Gate-Source Voltage	±20	V
lo	Drain Current – Continuous (T <sub>A</sub> =25°C)	300	mA
ID .	Drain Current – Continuous (T <sub>A</sub> =70°C)	240	mA
Ірм	Drain Current – Pulsed <sup>1</sup>	1.2	А
Po	Power Dissipation (T <sub>A</sub> =25°C)	313	mW
PD	Power Dissipation – Derate above 25°C	2.5	mW/°C
Тѕтс	Storage Temperature Range	-55 to 150	°C
TJ	Operating Junction Temperature Range	-55 to 150	℃

#### **Thermal Characteristics**

Symbol	ol Parameter		Max.	Unit
Reja	Thermal Resistance Junction to ambient		450	°C/W

# Electrical Characteristics (TJ=25 $^{\circ}$ C , unless otherwise noted)

#### Off Characteristics

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
BVDSS	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V , I <sub>D</sub> =250uA	55			V
△BVpss/△TJ	BVpss Temperature Coefficient	/DSS Temperature Coefficient Reference to 25°C , ID=1mA		0.05		V/°C
	Dunin Course Landson Course	V <sub>DS</sub> =48V , V <sub>GS</sub> =0V , T <sub>J</sub> =25°C			1	uA
loss	Drain-Source Leakage Current	V <sub>DS</sub> =55V , V <sub>GS</sub> =0V , T <sub>J</sub> =85°C			400	Α
lgss	Gate-Source Leakage Current	V <sub>GS</sub> = ±20V , V <sub>DS</sub> =0V			±6	uA



#### On Characteristics

RDS(ON)	Static Drain-Source On-Resistance	Vgs=10V , ID=0.3A		1.2	1.5	Ω
T CD3(ON)	otatio Brain Godroc On Noolotanoo	V <sub>GS</sub> =4.5V , I <sub>D</sub> =0.2A		1.5	2.3	
V <sub>GS(th)</sub>	Gate Threshold Voltage	-Vgs=Vps , Ip =250uA	0.8	1.1	1.6	V
△VGS(th)	V <sub>GS(th)</sub> Temperature Coefficient	V03-V03, ID-2000A		3		mV/°C

#### On Characteristics

Rds(on)	Static Drain-Source On-Resistance	Vgs=10V , Ib=0.3A		1.2	1.5	Ω
TXDS(ON)	Static Drain-Gource Off-Resistance	V <sub>GS</sub> =4.5V , I <sub>D</sub> =0.2A		1.5	2.3	
V <sub>GS(th)</sub>	Gate Threshold Voltage	-Ves=Vps , Ib =250uA	0.8	1.1	1.6	V
△VGS(th)	V <sub>GS(th)</sub> Temperature Coefficient	7 V 00 - V D0 , ID -230UA		3		mV/°C

### **Dynamic and switching Characteristics**

Ciss	Input Capacitance		 23	
Coss	Output Capacitance	V <sub>DS</sub> =30V , V <sub>GS</sub> =0V , F=1MHz	 16	 pF
Crss	Reverse Transfer Capacitance		 10	

**Drain-Source Diode Characteristics and Maximum Ratings** 

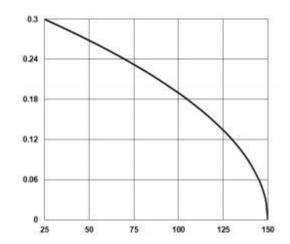
Symbol	Parameter	Parameter Conditions		Тур.	Max.	Unit
ls	Continuous Source Current	V <sub>G</sub> =V <sub>D</sub> =0V , Force Current			300	mA
Ism	Pulsed Source Current	vg-vb-ov, roice current			600	mA
Vsp	Diode Forward Voltage	Vgs=0V , Is=0.3A , TJ=25°C			1.4	V

#### Note

- ${\it 1. Repetitive \ Rating : \ Pulsed \ width \ limited \ by \ maximum \ junction \ temperature.}$
- 2. The data tested by pulsed , pulse width  $~\leq~300\,\text{us}$  , duty cycle  $~\leq~2\%$  .
- $\ \ 3.\ \ \, \text{Essentially independent of operating temperature}.$



-ID , Continuous Drain Current



TJ ,JunctionTemperature(°C)

Fig. 1 Continuous Drain Current vs. TC

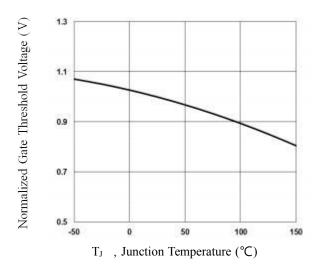
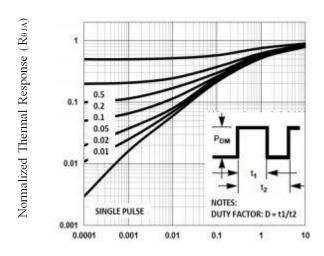
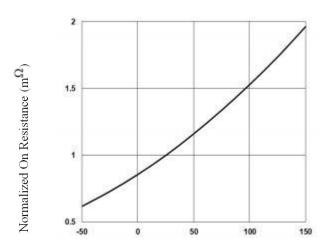


Fig. 3 Normalized Vth vs. TJ



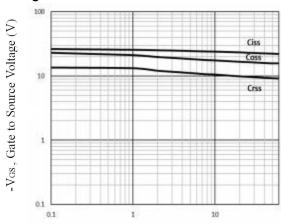
Square Wave Pulse Duration (s)

Fig. 5 Normalized Transient Response



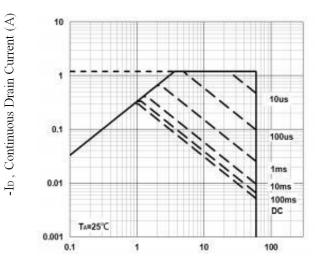
TJ, Juction Temperature(°C)

Fig. 2 Normalized RDSON vs. TJ



 $V_{\mathrm{DS}}$  , Drain to Source Voltage

Fig. 4 Capacitance Characteristics



V<sub>DS</sub>, Drain to Source Voltage(v)

Fig. 6 Maximum Safe Operation Area



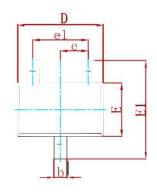


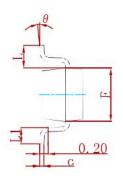


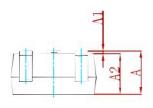




### PACKAGE MECHANICAL DATA

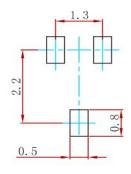






Symbol	Dimensions	In Millimeters	Dimensions	In Inches
Symbol	Min	Max	Min	Max
Α	0.900	1.100	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.000	0.035	0.039
b	0.200	0.400	0.008	0.016
С	0.080	0.150	0.003	0.006
D	2.000	2.200	0.079	0.087
Е	1.150	1.350	0.045	0.053
E1	2.150	2.450	0.085	0.096
е	0.650	) TYP	0.026	3 TYP
e1	1.200	1.400	0.047	0.055
L	0.525	REF	0.021	I REF
L1	0.260	0.460	0.010	0.018

# **Suggested Pad Layout**



- 1.Controlling dimension:in millimeters.
   2.General tolerance:±0.05mm.
- 3. The pad layout is for reference purposes only.

#### **REEL SPECIFICATION**

P/N	PKG	QTY
BSS138W-7-F-MS	SOT-323	3000



#### **Attention**

- Any and all MSKSEMI Semiconductor products described or contained herein do not have specifications that can handle applications that require extremely high levels of reliability, such as life-support systems, aircraft's control systems, or other applications whose failure can be reasonably expected to result in serious physical and/or material damage. Consult with your MSKSEMI Semiconductor representative nearest you before using any MSKSEMI Semiconductor products described or contained herein in such applications.
- MSKSEMI Semiconductor assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all MSKSEMI Semiconductor products described or contained herein.
- Specifications of any and all MSKSEMI Semiconductor products described or contained herein stipulate the performance, characteristics, and functions of the described products in the independent state, and are not guarantees of the performance, characteristics, and functions of the described products as mounted in the customer's products or equipment. To verify symptoms and states that cannot be evaluated in an independent device, the customer should always evaluate and test devices mounted in the customer'sproducts or equipment.
- MSKSEMI Semiconductor. strives to supply high-quality high-reliability products. However, any and all semiconductor products fail with someprobability. It is possiblethat these probabilistic failures could give rise to accidents or events that could endanger human lives, that could give rise to smoke or fire, or that could cause damage to other property. When designing equipment, adopt safety measures so that these kinds of accidents—or events cannot occur. Such measures include but are not limited to protective circuits anderror prevention circuitsfor safedesign, redundant design, and structural design.
- In the event that any or all MSKSEMI Semiconductor products (including technical data, services) described or contained herein are controlled under any of applicable local export control laws and regulations, such products must not be exported without obtaining the export license from theauthorities concerned in accordance with the above law.
- No part of this publication may be reproduced or transmitted in any form or by any means, electronic or mechanical, including photocopying and recording, or any information storage or retrieval system, or otherwise, without the prior written permission of MSKSEMI Semiconductor.
- Information (including circuit diagrams and circuit parameters) herein is for example only; it is not guaranteed for volume production. MSKSEMI Semiconductor believes information herein is accurate and reliable, but no guarantees are made or implied regarding its use or any infringements of intellectual property rights or other rights of third parties.
- Any and all information described or contained herein are subject to change without notice due to product/technology improvement, etc. Whendesigning equipment, referto the "Delivery Specification" for the MSKSEMI Semiconductor productthat you intend to use.

# **X-ON Electronics**

Largest Supplier of Electrical and Electronic Components

Click to view similar products for MOSFET category:

Click to view products by MSKSEMI manufacturer:

Other Similar products are found below:

IRFD120 JANTX2N5237 2SK2267(Q) BUK455-60A/B TK100A10N1,S4X(S MIC4420CM-TR VN1206L NDP4060 SI4482DY
IRS2092STRPBF-EL IPS70R2K0CEAKMA1 TK31J60W5,S1VQ(O TK31J60W,S1VQ(O TK16J60W,S1VQ(O 2SK2614(TE16L1,Q)
DMN1017UCP3-7 EFC2J004NUZTDG P85W28HP2F-7071 DMN1053UCP4-7 NTE2384 DMC2700UDMQ-7 DMN2080UCB4-7
DMN61D9UWQ-13 US6M2GTR DMN31D5UDJ-7 DMP22D4UFO-7B IPS60R3K4CEAKMA1 DMN1006UCA6-7 DMN16M9UCA6-7
STF5N65M6 IRF40H233XTMA1 STU5N65M6 DMN6022SSD-13 DMN13M9UCA6-7 DMTH10H4M6SPS-13 IPS60R360PFD7SAKMA1
DMN2990UFB-7B SSM3K35CT,L3F IPLK60R1K0PFD7ATMA1 2N7002W-G MCAC30N06Y-TP IPWS65R035CFD7AXKSA1
MCQ7328-TP SSM3J143TU,LXHF DMN12M3UCA6-7 PJMF280N65E1\_T0\_00201 PJMF380N65E1\_T0\_00201
PJMF280N60E1 T0 00201 PJMF600N65E1 T0 00201 PJMF900N65E1 T0 00201